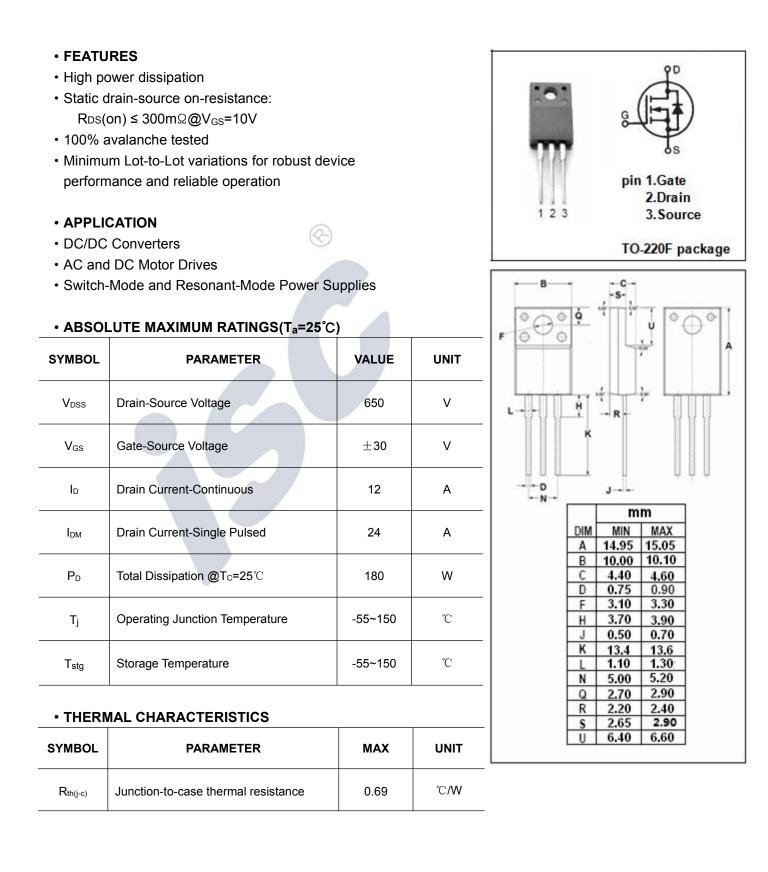


# isc N-Channel MOSFET Transistor

## IXTP12N65X2M



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#### **ELECTRICAL CHARACTERISTICS**

#### $T_{\text{C}}\text{=}25\,^\circ\!\!\!\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	МАХ	UNIT
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V; ID = 250 μ A	650			V
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> ; ID = 250 μ A	2.5		4.5	V
R <sub>DS(on)</sub>	Drain-Source On-Resistance	V <sub>GS</sub> =10V; I <sub>D</sub> = 6A			300	mΩ
I <sub>GSS</sub>	Gate-Source Leakage Current	$V_{GS}$ = ±30V; $V_{DS}$ =0V			±100	nA
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> = V <sub>DSS</sub> ; V <sub>GS</sub> = 0V			5	- μ <b>Α</b>
		V <sub>DS</sub> = V <sub>DSS</sub> ; V <sub>GS</sub> = 0V;TJ= 125℃			50	
$V_{\text{SD}}$	Diode forward voltage	I <sub>F</sub> = 12A; V <sub>GS</sub> = 0V			1.4	V

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